



Photodetectors are an integral part of optoelectronics devices owing to their wide applications in the field of optical sensors, satellite communication, spectroscopic techniques, biomedical imaging and other strategic areas of applications. Among these solar blind detectors are gaining attention from the scientific community worldwide owing to their potential applications in the missile communications and outer space applications. A variety of wide band gap materials have been reported in the literature in the past. However researchers at MNRG have recently reported solution processed CuO thin films for solar blind photo-detection utilizing the direct transition in these materials, which has been demonstrated for the first time in literature. The simple photoconductor device showed an encouraging responsivity of 7.8 A/W and specific detectivity of  $3.08 \times 10^{11} \text{ cm Hz}^{1/2} \text{ W}^{-1}$ . The UV-Vis rejection ratio was observed to be of three orders of magnitude. The article has been selected as editor's pick in IEEE Electron Device Letters. The work has tremendous potential for technological advancement in the field of solar blind detectors. The results are also of critical significance because CuO has traditionally been believed to be a material sensitive towards IR region of spectrum of light owing to their indirect transitions.

Ñ T Dixit et al, IEEE Electron Dev Lett, (2019, in press), DOI: 10.1109/LED.2018.2886928.

For more details about this work visit <http://www.iiti.ac.in/people/~vipul/>